

Technical Data Data Sheet N1250, Rev. A **Green Products**

20SQ045L SCHOTTKY BARRIER RECTIFIER

Applications:

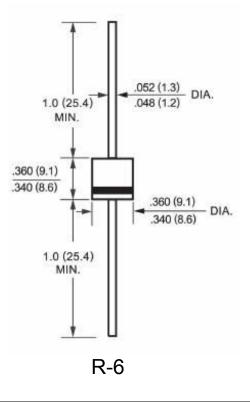
- DC-DC converters
- AC adapter
- High frequency rectification circuit
- Bypass diodes
- Photovoltaic Solar cell Protection Schottky Rectifier

Features:

- Super-high speed & low noise switching
- Low voltage drop
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches/ mm





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 FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



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Marking Diagram:



Where XXXXX is YYWWL

20	= Forward Current (20A)
S	= Package Type
Q	= Device Type
045	= Reverse Voltage (45V)
L	= Low VF
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
20SQ045L	R-6 (Pb-Free)	500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Rating:

Characteristics	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	Vrrm	-	45	V
Max. average forward current	I _{F(AV)}	R- load, Ta=25℃	20	Α
Surge(Non-repetitive) Forward Current	I _{FSM}	8.3ms single half sine-wave	350	А

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Electrical Characteristics (Ta=25°C Unless otherwise specified)

Characteristics	Symbol	Conditions		Max.	Unit
Peak Forward Voltage	Vfm	Ігм=20.0А,Та=25℃		0.50	V
Peak Forward Voltage	Vfm	Ігм=20.0А,Та=125℃		0.45	V
Peak Reverse Current	IRRM1	VRM=VRRM	Ta=25℃	1.0	mA
	IRRM2	VRM-VRRM	Ta=125℃	200	ША
Max. Junction Capacitance (per leg)	CT	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz		1300	pF
Thermal Resistance(Typical)	R θJ-c	Between junction and case		3.0	°C/W
	R θJ-L	Between junction and lead		2.0	

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units	
Junction Temperature	perature T_J At reduced reverse $V_R \leq 80\% V_{RRM}$		-55 to +125	°C	
		At reduced reverse voltage: $V_R \leqslant 50\% V_{RRM}$	-55 to +180		
		In DC forward mode	-55 to +200		
Storage Temperature	T _{stg}	-	-55 to +125	°C	
Approximate Weight	wt	-	2.24	g	
Case Style	R-6				

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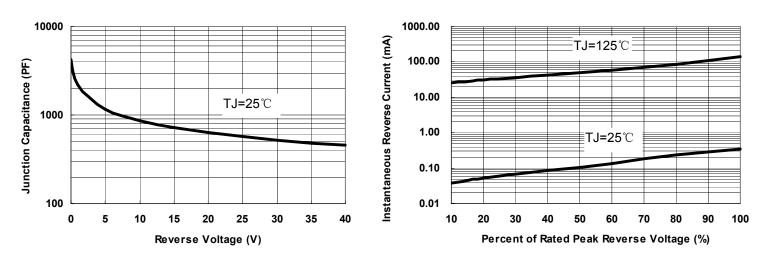




Fig.2-Typical Reverse Characteristics

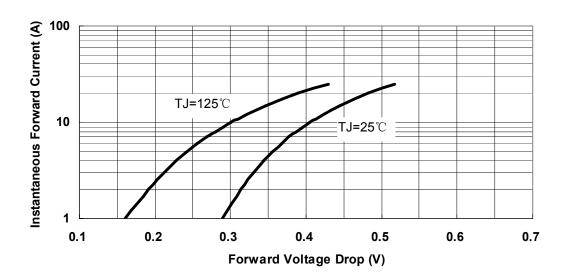


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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